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**DATASTAI**

## Advanced Search: INSPEC - 1969 to date (INZZ)

Search history:

No.	Database	Search term	Info added since	Results	
1	INZZ	dual WITH gate SAME amorphous	unrestricted	23	<a href="#">show titles</a>
2	INZZ	1 AND perovskite	unrestricted	0	-
3	INZZ	(dual OR stacked) WITH gate AND perovskite	unrestricted	0	-

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7/31/02

Select special search terms from the following list(s):

Sl	File	Search Text	DBs	Time Stamp
1	3757	257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:39
2	1150806	barium or strontium or titanium or lanthanum or zirconium or aluminum or STRONTIU or TITANIUM or LANTHANU or LLANTHANU or ZIRCONIUM or ALUMINUM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:39
3	1647	((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same \$4crystal\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:39
4	0	((fet or (field adj effect adj transistor)) and (gate same amorphous same \$4crystal\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:37
5	1117	(dual with gate with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:37
6	0	(dual with gate with layer) same (perovskite)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:37
7	2	(dual with gate with layer) same (silicon adj \$2oxide) same (strontium adj titanate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:37
8	3762	257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:39
9	1151252	barium or strontium or titanium or lanthanum or zirconium or aluminum or STRONTIU or TITANIUM or LANTHANU or LLANTHANU or ZIRCONIUM or ALUMINUM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:40
10	75	((dual with gate with layer) ) and (257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls. )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 09:44
11	1327	((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same (crystal\$4 or monocrystal\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:45
12	1	((dual with gate with layer) ) and (257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls. ) and perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 10:46
13	46	((dual or stacked) with gate) and perovskite	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 09:47

Good ref.

updated EAST 7/31/02